



### AS2333

1.8V, MICROPOWER

CMOS ZERO-DRIFT OPERATIONAL AMPLIFIERS

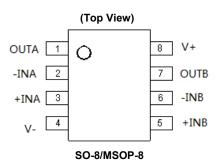
# Description

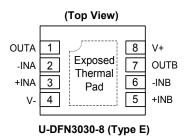
The AS2333 is dual CMOS operational amplifier designed with chopping stabilization technique. This product can provide ultra-low input offset voltage (8µV typical) and near zero-drift over time and temperature. This technique also eliminates 1/f noise and the cross-over distortion present in most rail-to-rail input operational amplifiers. The high-precision, low quiescent current amplifier offers high-impedance inputs that have a common-mode range 100mV beyond the rails, and a rail-to-rail output that swings within 50mV of the rails. Single or dual supplies as low as 1.8V ( $\pm$ 0.9V) and up to 5.5V ( $\pm$ 2.75V) can be used.

The device is optimized for low voltage single supply application, especially for low-power high-precision applications.

The AS2333 is available in the standard 8-pin SO-8, MSOP-8, and U-DFN3030-8 (Type E) packages, and is specified for operation from -40°C to +125°C.

## **Pin Assignments**





## Features

- Low Input Offset Voltage: 8µV (typ)
- Zero Drift: 0.02µV/°C (typ)
- 0.01Hz to 10Hz Noise:  $1.1 \mu V_{PP}$
- Low Quiescent Current: 12µA per Amplifier
- Supply Voltage: 1.8V to 5.5V
- Rail-to-Rail Input and Output
- Bandwidth 350kHz
- Slew Rate 0.12V/µs (typ)
- MSOP-8, SO-8, and U-DFN3030-8 (Type E) Packages
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

### Applications

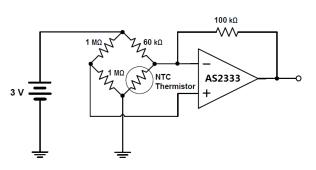
- Battery-Powered Instruments
- Handheld Test Equipment
- Medical Instrumentation
- Sensor Signal Conditioning
- Low Voltage Current Sensing

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

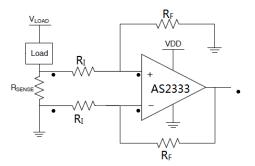
Notes:



# **Typical Application**



Thermistor Measurement



Low-Side Current Monitor

# **Pin Descriptions**

Pin Number	Pin Name	I/O	Description	
3	+INA	I	Noninverting input, channel A	
5	+INB	I	Noninverting input, channel B	
2	-INA	I	I Inverting input, channel A	
6	-INB	I	Inverting input, channel B	
1	OUTA	0	Output, channel A	
7	OUTB	0	Output, channel B	
8	V+	_	Positive Power Supply Recommend to place a minimum 0.1µF decoupling capacitor between V+ pin and GND as close as possible.	
4	V-	_	Negative Power Supply Single power supply application, it is normally tied to ground. Split power supply application, a minimum 0.1µF decouple capacitor is recommended to be placed between V- pin and GND as close as possible.	



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Symbol	Parameter	Rating	Rating	
$V_{\rm S}$ = V+ - V-	Supply Voltage Range	6.5		V
V <sub>-IN</sub> / V <sub>+IN</sub>	Signal Input Terminals (Note 5)	V 0.3V to V+	+ 0.3V	V
	Signal Input Terminals (Note 5)	-1 to +1		mA
	Output Short-Circuit (Note 6)	Continuo	JS	mA
T <sub>STG</sub>	Storage Temperature	-65 to +1	50	°C
TJ	Maximum Junction Temperature	+150		°C
T <sub>LEAD</sub>	Lead Temperature (Soldering, 10 Seconds)	+260		°C
	Junction-to-Ambient Thermal Resistance	SO-8	139	°C/W
$R_{ extsf{ heta}JA}$		MSOP-8	184	°C/W
		U-DFN3030-8 (Type E)	_	°C/W
		SO-8	25	°C/W
$R_{ extsf{ heta}JC}$	Junction-to-Case Thermal Resistance	MSOP-8	18	°C/W
		U-DFN3030-8 (Type E)	_	°C/W
ESD HBM	Human Body Model ESD Protection	4		kV
ESD CDM	Charged-Device Model ESD Protection	1		kV

### Absolute Maximum Ratings (Note 4) (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Notes: 4. Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended Operating Conditions indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.

Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3V beyond the supply rails should be current limited to 10mA or less.

6. Short-circuit to ground.

# Recommended Operating Conditions (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
V <sub>S</sub> = V+ - V-	Supply Voltage Range	1.8 to 5.5	V
TA	Operating Ambient Temperature Range	-40 to +125	°C



### **Electrical Characteristics** (@ $T_A = +25^{\circ}C$ , $V_S = 5.0V$ , $R_L = 10k\Omega$ connected to $V_S / 2$ , $V_{CM} = V_S / 2$ , and $V_{OUT} = V_S / 2$ , unless otherwise specified.)

Symbol	Parameter	Cor	nditions	Min	Тур	Мах	Unit
Offset Voltag	e	1					
V <sub>OS</sub>	Input Offset Voltage	V <sub>S</sub> = 5V		_	8	22	μV
		T <sub>A</sub> = -40°C to +8	5°C	—	0.02	0.1	μV/°C
$\Delta V_{OS} / \Delta T$	Input Offset Voltage Drift (Note 7)	T <sub>A</sub> = -40°C to +125°C		_		0.2	μV/°C
PSRR	Power-Supply Rejection Ratio	V <sub>S</sub> = 1.8V to 5.5' +125°C		_	1	5	μV/V
_	Long-Term Stability		_		(Note 7)		μV
_	Channel Separation, DC		_	_	0.1	_	μV/V
Input Bias Cu	irrent						
		T <sub>A</sub> = +25°C		_	±70	±200	
IB	Input Bias Current	T <sub>A</sub> = -40°C to +1	25°C	—	±400	_	pА
los	Input Offset Current		_	_	±140	±400	
Noise	P						
		f = 0.01Hz to 1H	Z	_	0.3	_	
V <sub>N</sub>	Input Voltage Noise	f = 0.1Hz to 10H		_	1.1	_	μV <sub>PP</sub>
IN	Input Current Noise	f = 10Hz			100	_	fA/√Hz
Input Voltage							
V <sub>CM</sub>	Common-Mode Voltage Range		_	(V-) - 0.1		(V+) + 0.1	V
CMRR	Common-Mode Rejection Ratio	$(V-) - 0.1V < V_{CM} < (V+) + 0.1V,$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		106	120		dB
Input Capacit	ance						
_	Differential	_		_	2	_	pF
	Common-Mode			_	4	_	pF
Open-Loop G	ain						
A <sub>OL</sub>	Open-Loop Voltage Gain	$(V-) + 100mV < V_O < (V+) - 100mV,$ $R_L = 10k\Omega, T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		106	130	_	dB
Frequency Re	esponse						
GBW	Gain-Bandwidth Product	C <sub>L</sub> = 100pF		_	350	_	kHz
SR	Slew Rate	G = +1		_	0.12	_	V/µs
Output	1	I.					
		Positive Rail	T <sub>A</sub> = +25°C	_	30	50	
		$R_L = 10k\Omega$	T <sub>A</sub> = -40°C to +125°C	_		70	
_	Voltage Output Swing from Rail	Negetice Dell	T <sub>A</sub> = +25°C	_	10	50	mV
		Negative Rail R <sub>L</sub> = 10kΩ	T <sub>A</sub> = -40°C to +125°C	_	_	70	
	Source Current			_	5	_	mA
Isc	Short-Circuit Current	Sink Current		_	25	_	mA
_	Open-Loop Output Impedance	f = 350kHz, I <sub>O</sub> = 0A		—	2	—	kΩ
Power Supply	<u> </u>	1					
Vs	Specified Voltage Range		_	1.8		5.5	V
		I <sub>O</sub> = 0A, T <sub>A</sub> = +2	5°C	_	12	20	-
lq	Quiescent Current per Amplifier	$I_0 = 0A, T_A = -40^{\circ}C \text{ to } +125^{\circ}C$				28	μA
· Q		$V_{\rm S} = 5V$				20	

Note:

7. 300-hour life test at +150°C demonstrated randomly distributed variation of approximately 1 $\mu$ V. This parameter guaranteed by design and characterization, not by testing.



40

38

36

34

30

28

26

24

22 20 -40 -25 -10

V<sub>s</sub> = 1.8V

Supply Current (µA) 32

# **Typical Performance Characteristics**

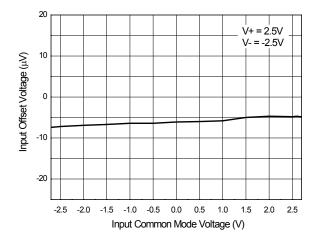
20 35 50 65 80 95 110 125

5



### Supply Current vs. Temperature

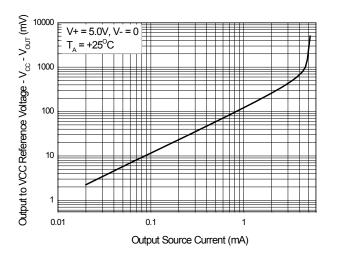




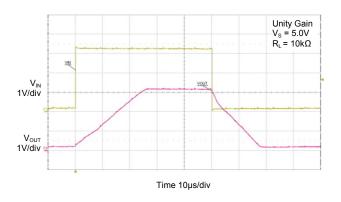
**Output Characteristics-Sourcing Current** 

Ambient Temperature (°C)

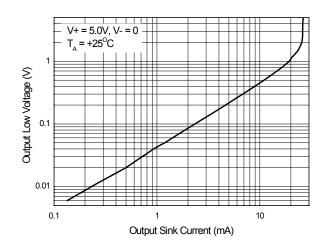
V\_ = 5V



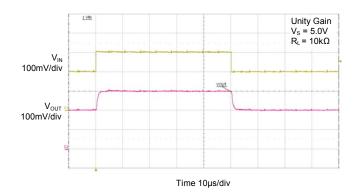




**Output Characteristics-Sinking Current** 

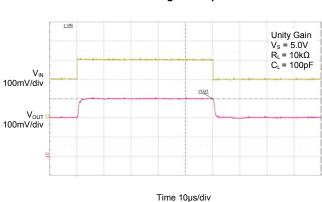


Small Signal Response

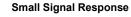


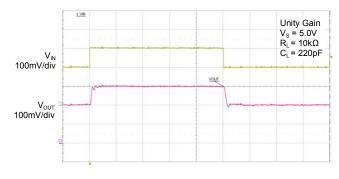


# Typical Performance Characteristics (continued)



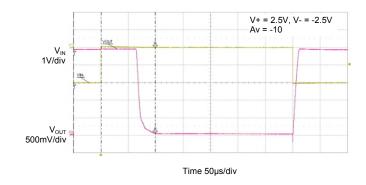
#### Small Signal Response



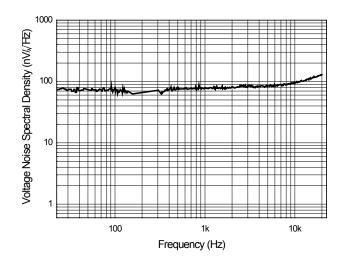


Time 10µs/div

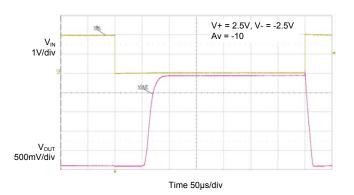
#### Positive Overvoltage Response



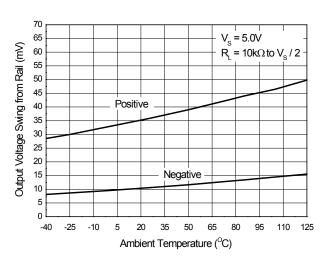
# Voltage Noise Spectral Density



Negative Overvoltage Response

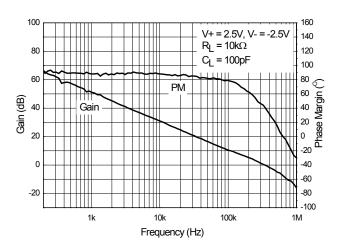


### Output Voltage Swing from Rail



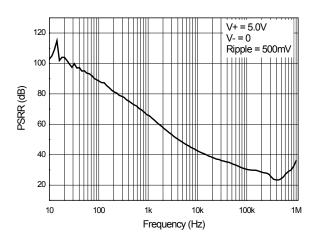


# Typical Performance Characteristics (continued)



### Frequency Response

Power Supply Rejection Ration vs. Frequency





## **Application Information**

### Overview

The AS2333 is low-power, zero-drift, high-precision, rail-to-rail input and output operational amplifier, which adopts chopper-stabilized function circuits to provide the advantage of minimizing input offset voltage and offset voltage drift over time and temperature. Its input common-mode voltage range extends 0.1V beyond the supply rails to allow for sensing near ground or system V<sub>DD</sub>. The device operates from a single-supply voltage as low as 1.8V, is unity-gain stable, has no 1/f noise, and has good PSRR and CMRR performance. These features make the AS2333 suitable for a wide range of general-purpose applications, especially for low-power and high-precision applications.

### Low Input Referred Noise

The device AS2333 is chopper-stabilized amplifier, which greatly reduces the flicker noise. The zero-drift chopper-stabilized amplifiers are especially suited for accurate, high-gain amplification at lower frequencies. In general, they do not exhibit the higher bandwidth of linear operational amplifiers, and the location of their clock frequency establishes a practical frequency limit on signal fidelity. This makes performance at low frequencies especially important, and the chopper-stabilized architecture further contributes to low-frequency usefulness by eliminating the classic linear operational amplifier 1/f input voltage noise. Many high-gain sensor applications are at low frequencies, making zero-drift amplifiers a natural choice for this function.

The below graphs compare the voltage noise density behaviors of conventional amplifiers and zero-drift amplifiers. The 1/f noise elimination in zero-drift amplifiers allow the AS2333 to have much lower noise at DC and low frequencies compared to the conventional low-noise amplifiers.

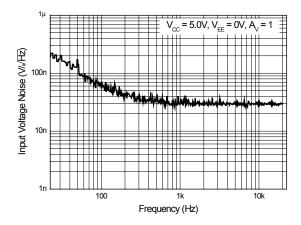
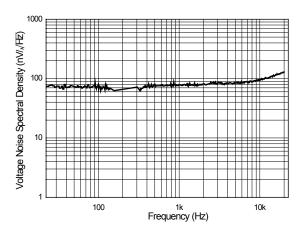


Figure 1. Input Voltage Noise in Conventional Amplifier (AZV832)





### Driving a Capacitive Load

The AS2333 can directly drive 200pF in unity-gain without oscillation. The unity-gain follower is the most sensitive configuration to capacitive loading. Capacitive loading directly on the output terminal can decrease the device's phase margin, leading to high-frequency ringing or oscillation.

To drive a heavier capacitive load, the circuit in Figure 3 can be used. The resistor  $R_{NULL}$  and  $C_L$  form a pole to increase stability by adding more phase margin to the system. The bigger the  $R_{NULL}$  resistor value, the more stable  $V_{OUT}$  is. Figure 4 and Figure 5 show the AS2333's output pulse response waveforms with and without  $R_{NULL}$  330 $\Omega$  for load conditions  $C_L$  = 470pF and  $R_L$  = 10k $\Omega$ .



## AS2333

## Application Information (continued)

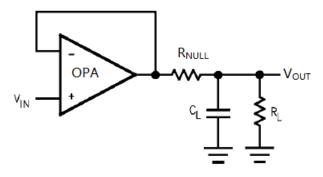


Figure 3. Capacitive Load with RNULL

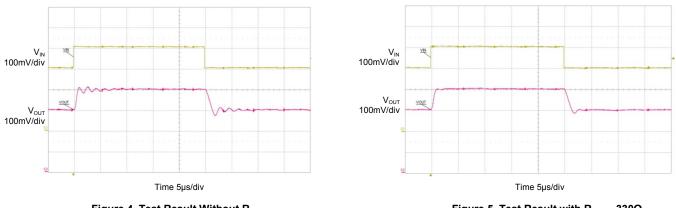


Figure 4. Test Result Without R<sub>NULL</sub>

Figure 5. Test Result with  $R_{\text{NULL}}\,330\Omega$ 

An RC snubber circuit can be used to reduce capacitive load ringing and overshoot, as shown in Figure 6. It allows the amplifier to drive larger values of capacitance while maintaining a minimum for overshoot and ringing. Figure 7 shows AS2333's test results for capacitive load 470pF with a snubber circuit.

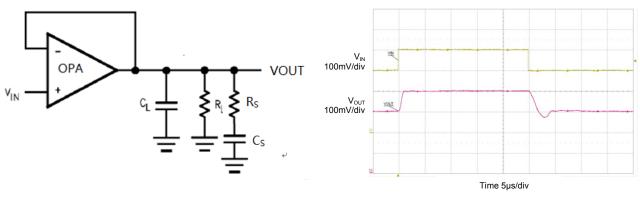


Figure 6. Circuit with Snubber Circuit

Figure 7. Test Result with Snubber Circuit



### AS2333

### Application Information (continued)

#### Low-Side Current Monitor Application

Low-side current sensing is used to monitor the current through a load. This method can be used to detect over-current conditions and is often used in feedback control, as shown in Figure 8. A sense resistor is placed in series with the load to the ground. Precision resistors are required for high accuracy and the resulting voltage drop is amplified using the AS2333.

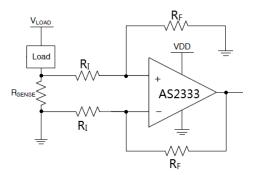


Figure 8. Low-Side Current Monitor Application

#### **Differential Amplifier for Bridged Circuits**

Sensors to measure strain, pressure, and temperature are often configured in a Wheatstone bridge circuit, as shown in Figure 9. In the measurement, the voltage change that is produced is relatively small and needs to be amplified before going into an ADC. Precision amplifiers are recommended in these types of applications due to their high gain, low noise, and low offset voltage.

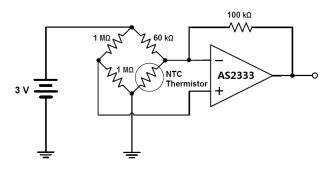
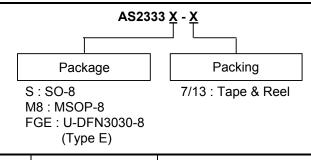


Figure 9. Bridge Circuit Amplification



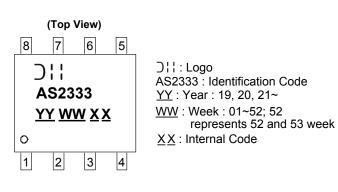
### Ordering Information



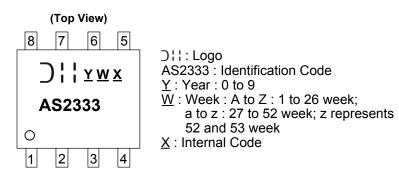
Part Number	Identification	Paakaging	Tape and Reel		
Fart Nulliger	Code	Packaging	Quantity	Part Number Suffix	
AS2333S-13	AS2333	SO-8	2500/Tape & Reel	-13	
AS2333M8-13	AS2333	MSOP-8	2500/Tape & Reel	-13	
AS2333FGE-7	ND	U-DFN3030-8 (Type E)	3000/Tape & Reel	-7	

## **Marking Information**

(1) SO-8



(2) MSOP-8



### (3) U-DFN3030-8 (Type E)

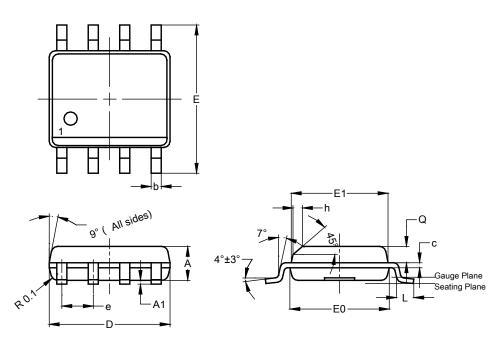
(Top View)	
ND	ND : Identification Code <u>Y</u> : Year : 0~9 <u>W</u> : Week : A~Z : 1~26 week;
<u>YWX</u>	a~z : 27~52 week; z represents
●	52 and 53 week
	X : Internal Code



# **Package Outline Dimensions**

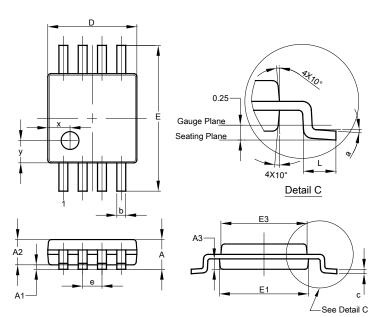
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SO-8



	S	<b>D-8</b>	
Dim	Min	Max	Тур
Α	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
С	0.15	0.25	0.20
D	4.85	4.95	4.90
Е	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
е			1.27
h			0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All	Dimens	ions in	mm

### (2) Package Type: MSOP-8



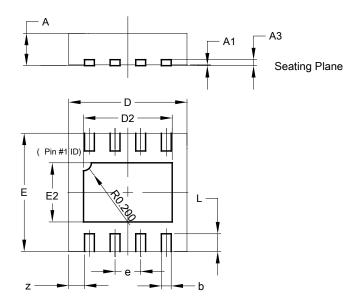
MSOP-8				
Dim	Min	Max	Тур	
Α	-	1.10	-	
A1	0.05	0.15	0.10	
A2	0.75	0.95	0.86	
A3	0.29	0.49	0.39	
b	0.22	0.38	0.30	
С	0.08	0.23	0.15	
D	2.90	3.10	3.00	
Е	4.70	5.10	4.90	
E1	2.90	3.10	3.00	
E3	2.85	3.05	2.95	
e	-	1	0.65	
L	0.40	0.80	0.60	
а	0°	8°	4°	
x	-	-	0.750	
у	-	-	0.750	
	Dimen	sions	in mm	



# Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(3) Package Type: U-DFN3030-8 (Type E)



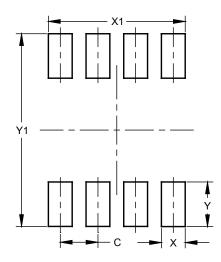
	U-DFN3030-8					
		pe E)				
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00	0.05	0.02			
A3	-	-	0.15			
b	0.20	0.30	0.25			
D	2.95	3.05	3.00			
D2	2.15	2.35	2.25			
Е	2.95	3.05	3.00			
E2	1.40	1.60	1.50			
е	-	-	0.65			
L	0.30	0.60	0.45			
z	-	-	0.40			
AI	l Dimens	sions in	mm			



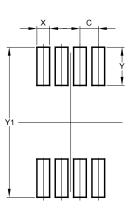
# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

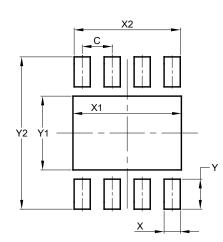
(1) Package Type: SO-8



(2) Package Type: MSOP-8



### (3) Package Type: U-DFN3030-8 (Type E)



Dimensions	Value (in mm)
C	0.650
Х	0.450
Y	1.350
Y1	5.300

Dimensions	Value (in mm)
C	0.650
Х	0.350
X1	2.350
X2	2.300
Y	0.650
Y1	1.600
Y2	3.300



### **Mechanical Data**

### SO-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.075 grams (Approximate)

#### MSOP-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.025 grams (Approximate)

### U-DFN3030-8 (Type E)

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Lead-Frame Solderable per MIL-STD-202, Method 208 4
- Weight: 0.017 grams (Approximate)



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